Supertex inc.

Advanced Information

High Voltage EL Lamp Driver

Ordering Information

	Package Options		Options
Device	Input Voltage	8-Lead SO	Die
HV824	1.0V to 1.6V	HV824LG	HV824X

F	6 2	tı	ır	20

☐ Processed with	HVCMOS®	technology
------------------	---------	------------

☐ 1.0V to 1.6V supply voltage

\neg	DC	4-	A (C		:
- 1	טט	το	AU	con	version

Permits the	use of high	n-resistance	elastomeric	lamp
connectors				

Adjustable output lamp frequency to control lamp	color,
lamp life, and power consumption	

Adjustable converter frequency to eliminate harmonics	and
optimize power consumption	

	Ena	hla	/dic	abla	fur	otion	-
1 1	⊏⊓a	Die	/นเรล	abie	ıuı	ictioi	

LOW	current	draw	under no	load	condition
LOW	current	uraw	under no	ioau	Condition

Applications

	Pagers
--	--------

	Portable	Instrume	ntation
--	----------	----------	---------

	Cel	lul	lar	Ph	or	es

General Description

The Supertex HV824 is a high voltage driver designed to drive EL lamps with capacitive loads of 2nF to 15nF. The input supply voltage range is 1.0V to1.6V. The device uses a single inductor and a minimum number of passive components. Typical output voltage applied to the EL lamp is 120V to 150V peak-to-peak. The HV824 can be enabled/disabled by connecting the $R_{\rm SW}$ resistor to $V_{\rm DD}/{\rm ground}$. In die form, the device has an enable bar pad which enables the IC when it is at logic low.

The HV824 has two internal oscillators, a switching MOSFET, and a high voltage EL lamp driver. The frequency for the switching MOSFET is set by an external resistor connected between the $R_{\text{sw-osc}}$ pin and the V_{DD} pin. The EL lamp driver frequency is set by an external resistor connected between the $R_{\text{EL-osc}}$ pin and the V_{DD} pin. An external inductor is connected between the L_x and V_{DD} pins. A $0.01\mu\text{F}$ to $0.1\mu\text{F}$ capacitor is connected between C_s and GND pins. The EL lamp is connected between V_A and V_B .

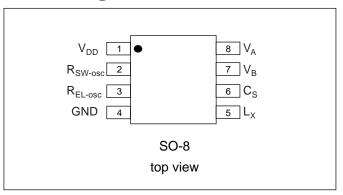
The switching MOSFET charges the external inductor and discharges it into the $0.01\mu F$ to $0.1\mu F$ capacitor at C_s . The voltage at C_s will start to increase. Once the voltage at C_s reaches a nominal value of 75V, the switching MOSFET is turned OFF to conserve power. The outputs V_A and V_B are configured as an H-bridge and are switching in opposite states to achieve a maximum voltage of 180V peak-to-peak across the EL lamp.

Absolute Maximum Ratings*

Supply Voltage, $V_{\rm DD}$	-0.5V to +2.0V
Output Voltage, V _{Cs}	-0.5V to +120V
Operating Temperature Range	-25°C to +85°C
Storage Temperature Range	-65°C to +150°C
Power Dissipation	400mW

Note

Pin Configuration



^{*}All voltages are referenced to GND.

Electrical Characteristics

DC Characteristics (Over recommended operating conditions unless otherwise specified, $T_A = 25^{\circ}C$)

Symbol	Parameter	Min	Тур	Max	Units	Conditions
I _{DDQ}	Quiescent V _{DD} supply current		50	100	nA	R _{SW-osc} =Low
I _{DD}	Input current going into the V _{DD} pin			450	μА	V _{DD} =1.5V.
I _{IN}	Input current including inductor current.			70	mA	V _{DD} =1.5V. See Figure 1.
V _{P-P}	Output voltage peak-to-peak	140	150	160	V	V _{DD} =1.5V. See Figure 1.
, b-b		130				V _{DD} =1.0V. See Figure 1.
f _{EL}	V _{A-B} output drive frequency	300	333		Hz	V _{DD} =1.5V. See Figure 1.
D	Switching transistor duty cycle		88		%	
C _{LOAD}	EL panel capacitance load range	2.0		15	nF	

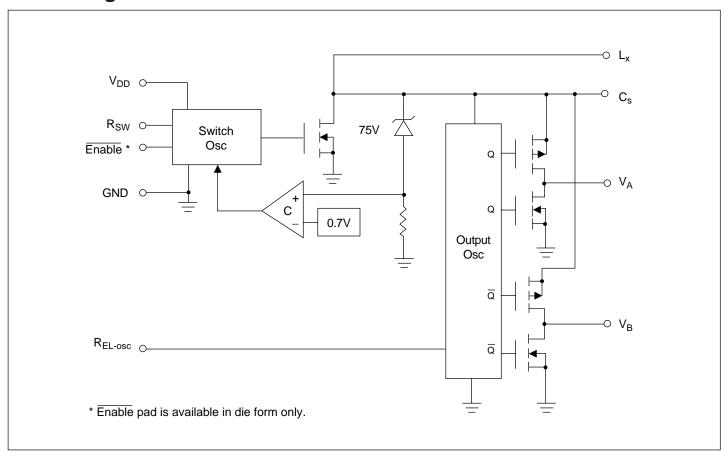
Recommended Operating Conditions

Symbol	Parameter	Min	Тур	Max	Units	Conditions
V _{DD}	Supply voltage	1.0		1.6	V	
T _A	Operating temperature	-25		85	°C	

Enable/Disable Table

Sym	nbol	Parameter	Min	Тур	Max	Units	Conditions
V	' _{IL}	Low level input voltage to R _{SW} resistor	0		0.2	V	V _{DD} =1.0V to 1.6V.
V	, IH	High level input voltage to R _{SW} resistor	V _{DD} -0.5		V _{DD}	V	V _{DD} =1.0V to 1.6V.

Block Diagram



Typical Application

